

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
800V	$4.4\Omega@10V$	2A



合肥矽普半导体

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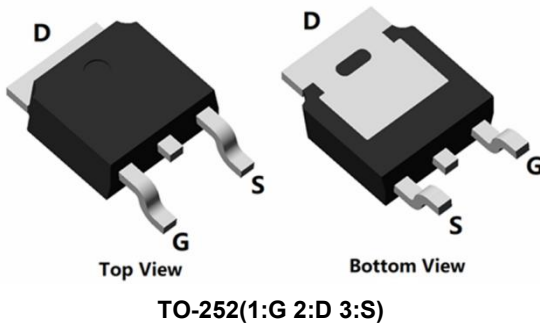
Feature

- Fast Switching
- Low Gate Charge and $R_{DS(on)}$
- 100% Single Pulse avalanche energy Test

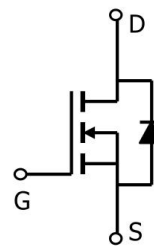
Applications

- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

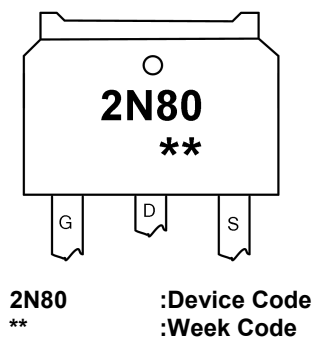
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
SP2N80TH	TO-252	2500

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ($T_C=25^\circ\text{C}$)	I_D	2	A
Continuous Drain Current ($T_C=100^\circ\text{C}$)	I_D	1.3	A
Pulsed Drain Current	I_{DM}	8	A
Single Pulse Avalanche Energy ¹	E_{AS}	45	mJ
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	87	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.43	$^\circ\text{C/W}$
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

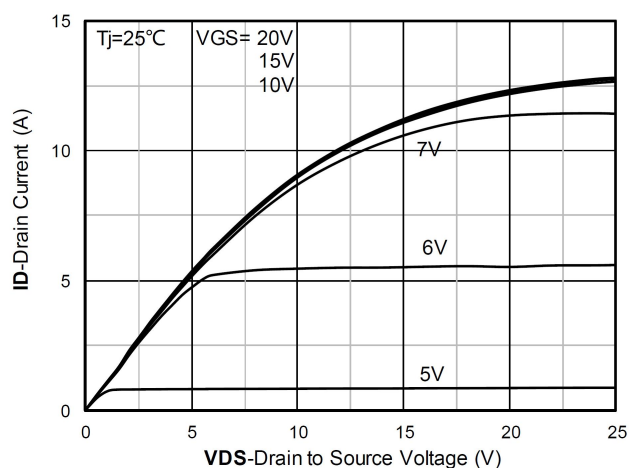
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	800	-	-	V
Drain-Source Leakage Current	IDSS	VDS=640V , VGS=0V , TJ=25℃	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±30V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	3.0	4.0	5.0	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=1A	-	4.4	5.5	Ω
Dynamic characteristics						
Input Capacitance	Ciss	VDS=25V , VGS=0V , f=1MHz	-	380	-	pF
Output Capacitance	Coss		-	40	-	
Reverse Transfer Capacitance	Crss		-	1.6	-	
Total Gate Charge	Qg	VDS=640V , VGS=10V , ID=2A	-	9.6	-	nC
Gate-Source Charge	Qgs		-	2.3	-	
Gate-Drain Charge	Qgd		-	4.6	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=400V VGS=10V , RG=25Ω, ID=2A	-	12.6	-	nS
Rise Time	Tr		-	23	-	
Turn-Off Delay Time	Td(off)		-	26	-	
Fall Time	Tf		-	26.6	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	2	A
Reverse Recovery Time	Trr	IS=2A, di/dt=100A/us, TJ=25℃	-	365	-	nS
Reverse Recovery Charge	Qrr		-	1.2	-	uC

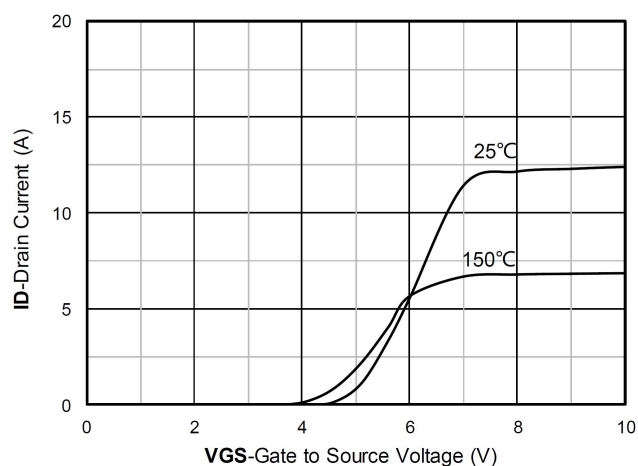
Note :

- The EAS test condition is $V_{DD}=50V, V_{GS}=10V, L=10mH, R_G=25\Omega$

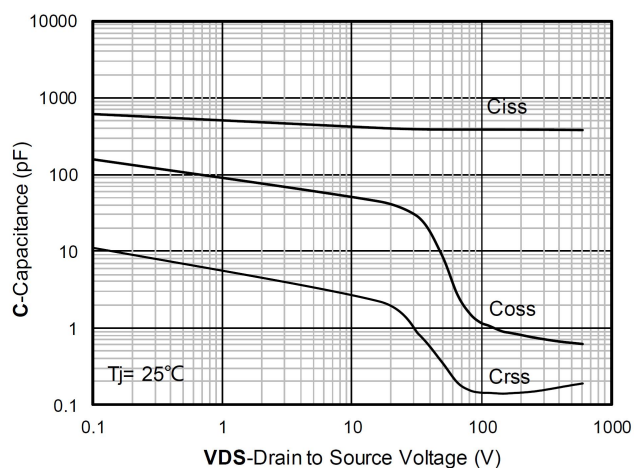
Typical Characteristics



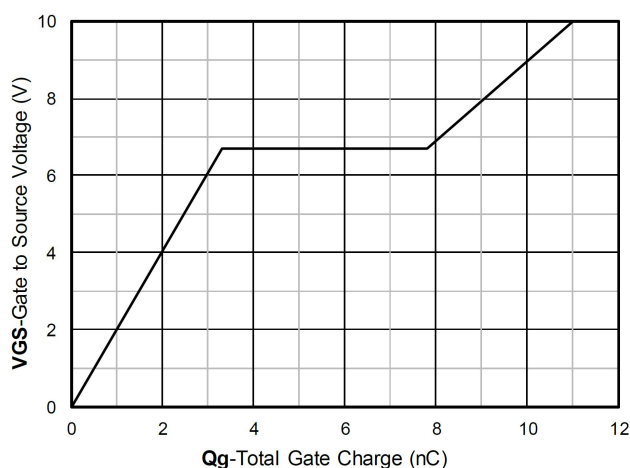
Output Characteristics



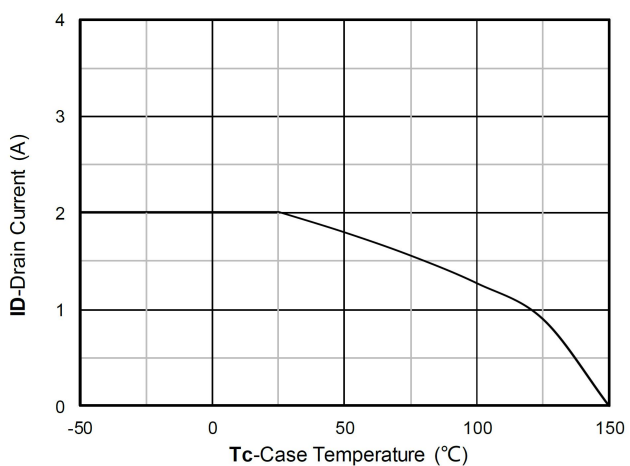
Transfer Characteristics



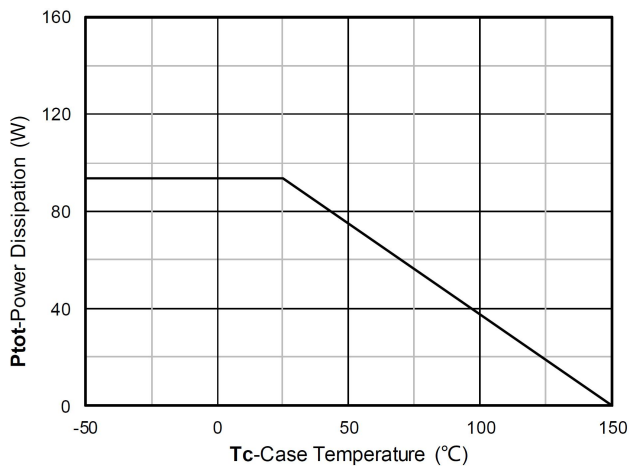
Capacitance Characteristics



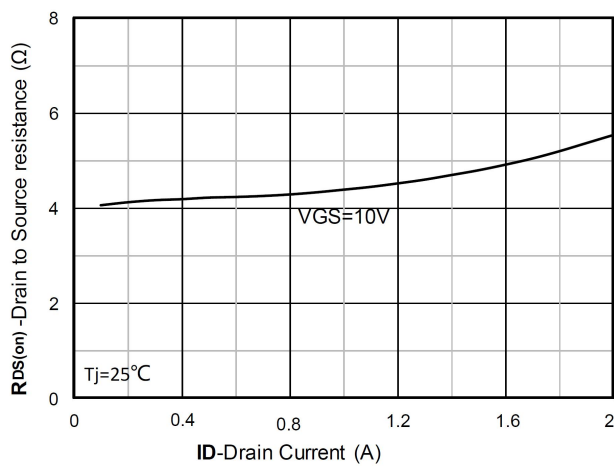
Gate Charge



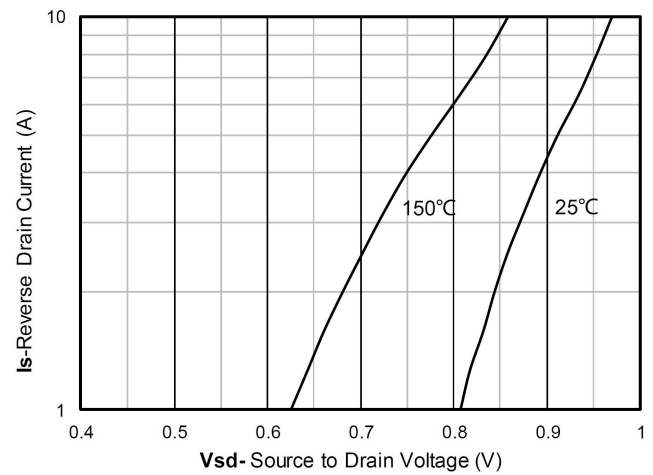
Current dissipation



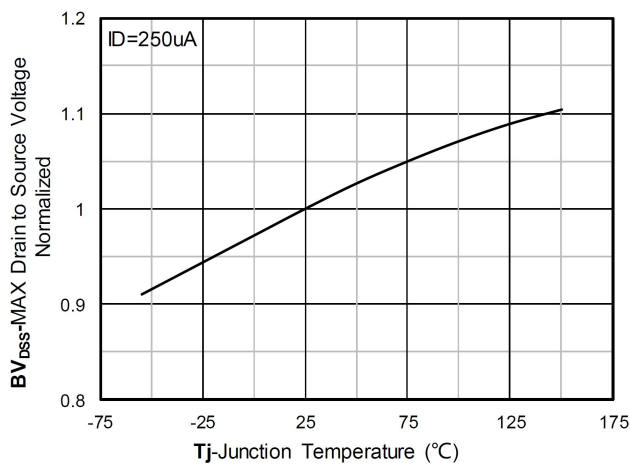
Power dissipation



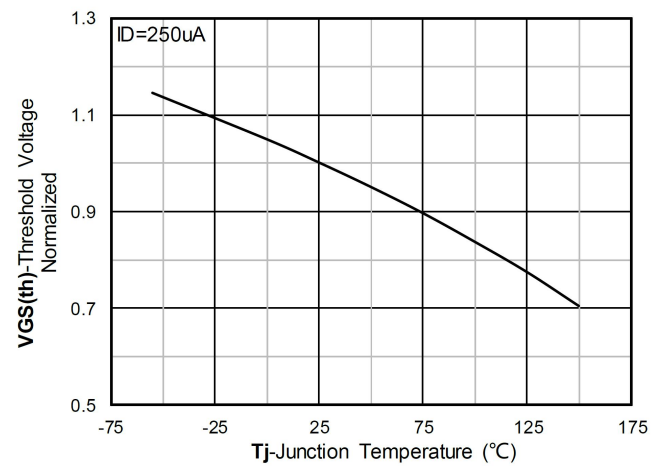
$R_{DS(on)}$ VS Drain Current



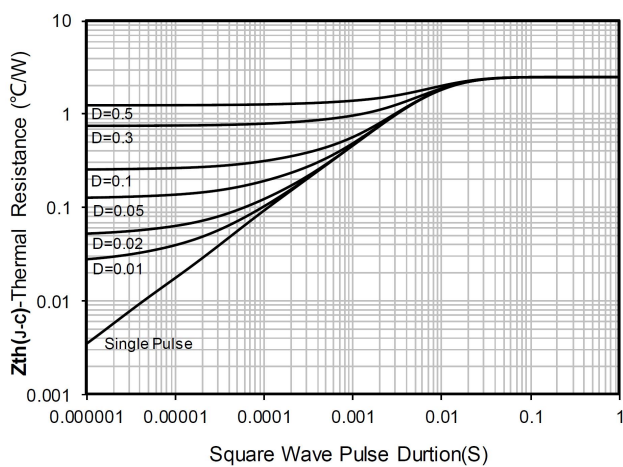
Forward characteristics of reverse diode



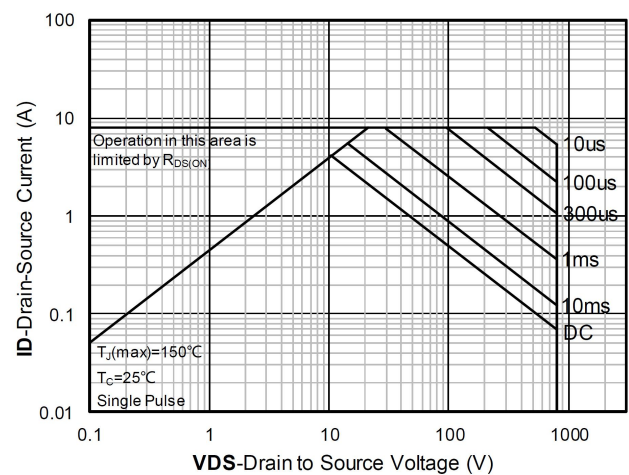
Normalized breakdown voltage



Normalized Threshold voltage

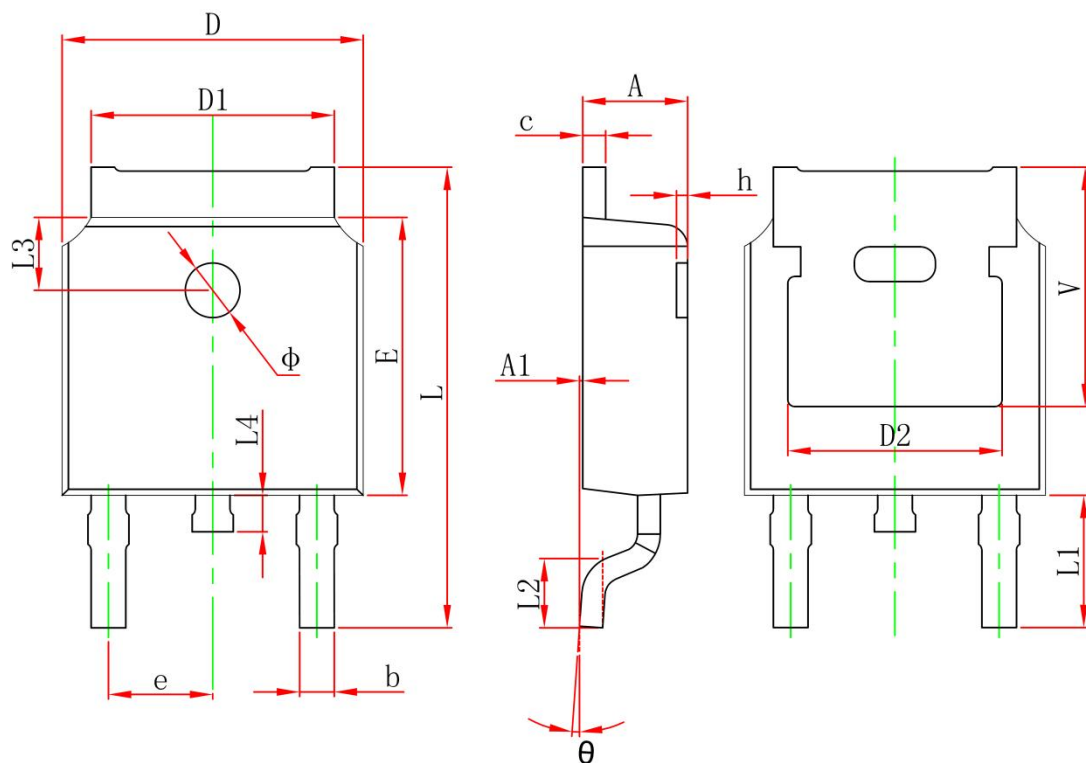


Maximum Transient Thermal Impedance



Safe Operation Area

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	